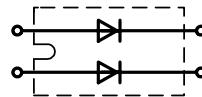


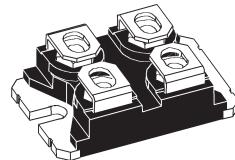
## Power Schottky Rectifier

$I_{FAV} = 2 \times 100 \text{ A}$   
 $V_{RRM} = 150 \text{ V}$   
 $V_F = 0.77 \text{ V}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
150	150	DSS 2x101-015A



miniBLOC,  
SOT-227 B



Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		150	A
$I_{FAVM}$	$T_C = 110^\circ\text{C}$ ; rectangular, $d = 0.5$	100	A
$I_{FAVM}$	$T_C = 110^\circ\text{C}$ ; rectangular, $d = 0.5$ ; per device	200	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	1200	A
$E_{AS}$	$I_{AS} = 4 \text{ A}$ ; $L = 100 \mu\text{H}$ ; $T_{VJ} = 25^\circ\text{C}$ ; non repetitive	0.8	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$ ; repetitive	0.4	A
$(dv/dt)_{cr}$		18	kV/ $\mu$ s
$T_{VJ}$		-40...+150	°C
$T_{VJM}$		150	°C
$T_{stg}$		-40...+150	°C
$P_{tot}$	$T_C = 25^\circ\text{C}$	310	W
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
$M_d$	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
<b>Weight</b>	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$	① $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	4 40	mA mA
$V_F$	$I_F = 100 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$ $I_F = 100 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$ $I_F = 200 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$	0.77 0.91 0.99	V V V
$R_{thJC}$ $R_{thCH}$		0.4 0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
Data according to IEC 60747 and per diode unless otherwise specified

### Features

- International standard package miniBLOC
- Isolation voltage 2500 V~
- UL registered E 72873
- 2 independent Schottky diodes in 1 package
- Very low  $V_F$
- Extremely low switching losses
- Low  $I_{RM}$ -values

### Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see Outlines.pdf

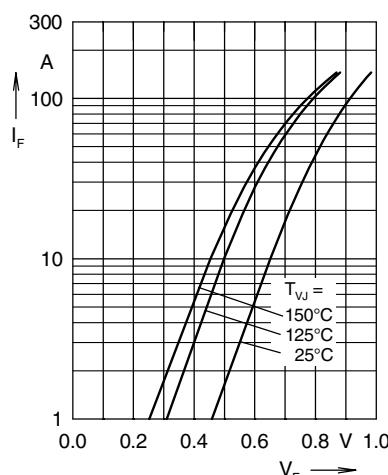


Fig. 1 Maximum forward voltage drop characteristics

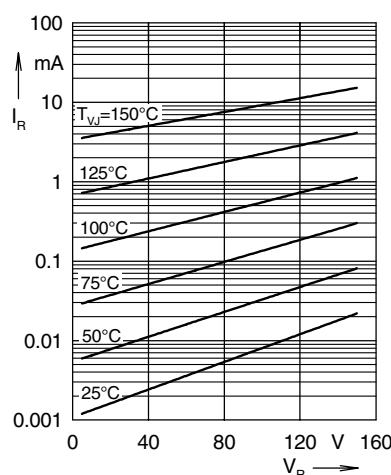


Fig. 2 Typ. value of reverse current  $I_R$  versus reverse voltage  $V_R$

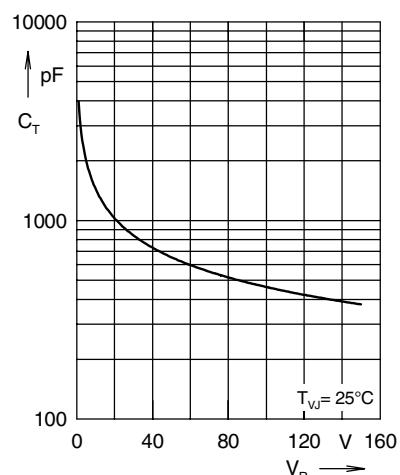


Fig. 3 Typ. junction capacitance  $C_T$  versus reverse voltage  $V_R$

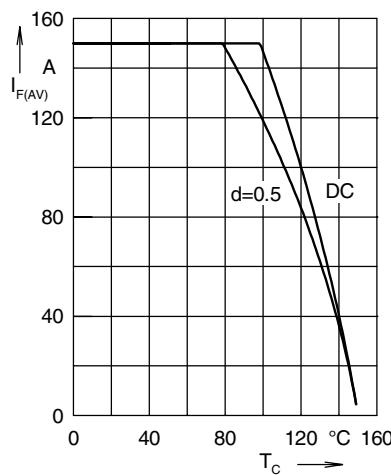


Fig. 4 Average forward current  $I_{F(AV)}$  versus case temperature  $T_C$

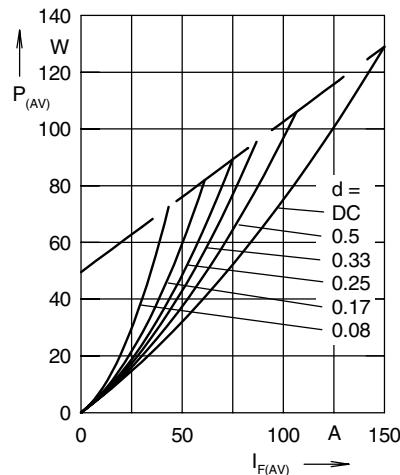


Fig. 5 Forward power loss characteristics

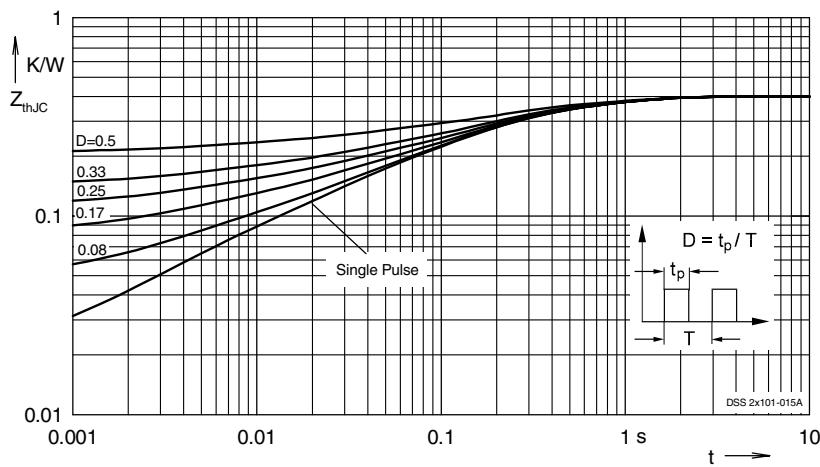


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

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